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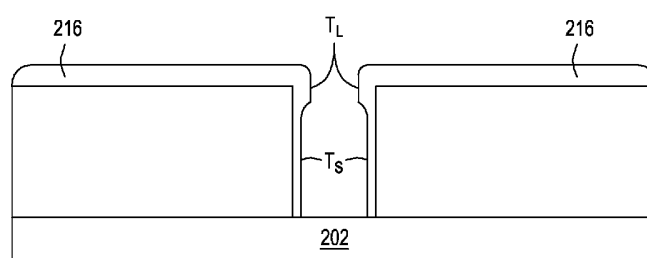


FIG. 2C

(57) Abstract: Methods and apparatus for processing a substrate are provided. For example, a method includes sputtering a material from a target in a PVD chamber to form a material layer on a layer comprising a feature of the substrate, the feature having an opening width defined by a first sidewall and a second sidewall, the material layer having a greater lateral thickness at the top surface of the layer than a thickness on the first sidewall or the second sidewall within the feature, depositing additional material on the layer by biasing the layer with an RF bias at a low power, etching the material layer from the layer by biasing the layer with an RF bias at a high-power, and repeatedly alternating between the low power and the high-power at a predetermined frequency.



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